



### **AOTF11N60L Information**



For Reference Only

Part Number AOTF11N60L

ManufacturerAlpha & Omega Semiconductor Inc.CategoryDiscrete Semiconductor Products<br/>Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 600V 11A TO220F

Package TO-220-3 Full Pack

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## **AOTF11N60L Specifications**

Manufacturer Part Number         AOTF11N60L           Manufacturer         Alpha & Omega Semiconductor Inc.           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3 Full Pack           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         11A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4.5V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         37nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1990pF @ 25V           Vgs (Max)         ± 30V           FET Feature         -           Power Dissipation (Max)         37.9W (Tc)           Rds On (Max) @ Id, Vgs         650 mOhm @ 5.5A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3F           Package / Case         TO-220-3 Full Pack		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3 Full Pack           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         11A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4.5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         37nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1990pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         37.9W (Tc)           Rds On (Max) @ Id, Vgs         650 mOhm @ 5.5A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3F           Package / Case         TO-220-3 Full Pack	Manufacturer Part Number	AOTF11N60L
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Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         11A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4.5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         37nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1990pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         37.9W (Tc)           Rds On (Max) @ Id, Vgs         650 mOhm @ 5.5A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3F           Package / Case         TO-220-3 Full Pack		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 11A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 37nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1990pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 37.9W (Tc) Rds On (Max) @ Id, Vgs 650 mOhm @ 5.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3F Package / Case	Package	TO-220-3 Full Pack
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C11A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 250μAGate Charge (Qg) (Max) @ Vgs37nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1990pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)37.9W (Tc)Rds On (Max) @ Id, Vgs650 mOhm @ 5.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3FPackage / CaseTO-220-3 Full Pack	Series	-
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Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  10V  Vgs(th) (Max) @ Id  4.5V @ 250μA  Gate Charge (Qg) (Max) @ Vgs  37nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  1990pF @ 25V  Vgs (Max)  ±30V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  650 mOhm @ 5.5A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3 Full Pack	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 250μAGate Charge (Qg) (Max) @ Vgs37nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1990pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)37.9W (Tc)Rds On (Max) @ Id, Vgs650 mOhm @ 5.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3FPackage / CaseTO-220-3 Full Pack	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  1990pF @ 25V  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Supplier Device Package  Package / Case  4.5V @ 250μA  5.5V @ 250μA  5	Current - Continuous Drain (Id) @ 25°C	11A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  1990pF @ 25V  Vgs (Max)  ±30V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  650 mOhm @ 5.5A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3F  Package / Case  TO-220-3 Full Pack	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Through Hole  Supplier Device Package  Package / Case  1990pF @ 25V  1990pF @ 25V  1900pF @ 2	Vgs(th) (Max) @ Id	4.5V @ 250μA
Vgs (Max) ±30V  FET Feature -  Power Dissipation (Max) 37.9W (Tc)  Rds On (Max) @ Id, Vgs 650 mOhm @ 5.5A, 10V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220-3F  Package / Case TO-220-3 Full Pack	Gate Charge (Qg) (Max) @ Vgs	37nC @ 10V
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Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  650 mOhm @ 5.5A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3F  Package / Case  TO-220-3 Full Pack	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs650 mOhm @ 5.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3FPackage / CaseTO-220-3 Full Pack	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3F  Package / Case  TO-220-3 Full Pack	Power Dissipation (Max)	37.9W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	Rds On (Max) @ Id, Vgs	650 mOhm @ 5.5A, 10V
Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3 Full Pack	Mounting Type	Through Hole
	Supplier Device Package	TO-220-3F
Report errors?	Package / Case	TO-220-3 Full Pack
		Report errors?

#### **AOTF11N60L Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **AOTF11N60L Payment Methods**





















### **AOTF11N60L Shipping Methods**













If you have any question about AOTF11N60L, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com